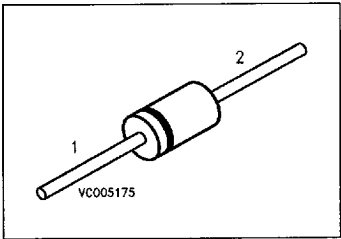


Silicon PIN Diode

BA 389

- Current-controlled RF resistor for switching and attenuating applications
- Frequency range
1 MHz ... 1 GHz
- Not for new design



Type	Marking	Ordering Code	Pin Configuration	Package ¹⁾
BA 389	yellow	Q62702-A732		DO-35 DHD

Maximum Ratings

Parameter	Symbol	Values	Unit
Reverse voltage	V_R	30	V
Forward current	I_F	50	mA
Junction temperature	T_j	150	°C
Storage temperature range	T_{slg}	- 65 ... + 150	

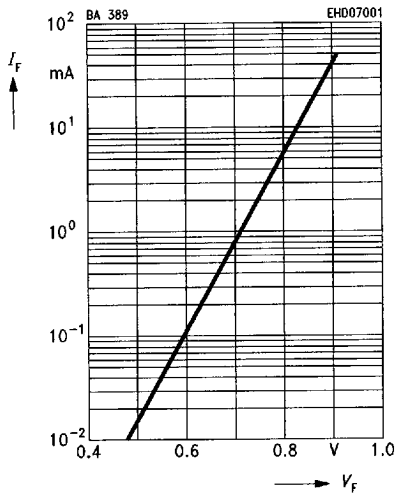
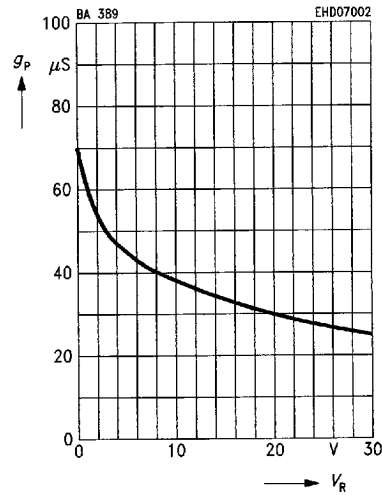
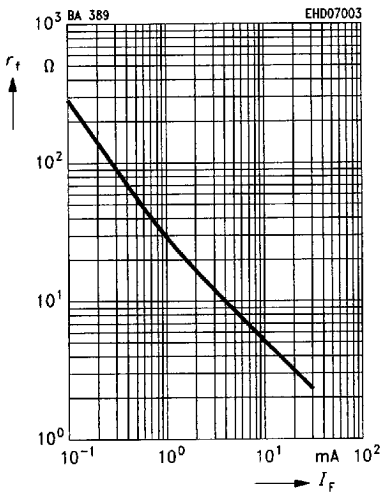
Thermal Resistance

Junction - ambient	$R_{th JA}$	≤ 400	K/W
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¹⁾ For detailed information see chapter Package Outlines.

Electrical Characteristicsat $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Forward voltage $I_F = 50\text{ mA}$	V_F	—	—	1	V
Reverse current $V_R = 30\text{ V}$	I_R	—	—	50	nA
Diode capacitance $V_R = 10\text{ V}, f = 1\text{ MHz}$ $V_R = 0\text{ V}, f = 100\text{ MHz}$	C_T	— —	0.55 0.35	— 0.5	pF
Forward resistance $f = 100\text{ MHz}$ $I_F = 1.5\text{ mA}$ $I_F = 10\text{ mA}$	r_f	— —	25 5	40 7.5	Ω
Zero bias conductance $V_R = 0\text{ V}, f = 100\text{ MHz}$	g_p	—	70	—	μS
Series inductance	L_s	—	2.5	—	nH

Forward characteristics $I_F = f(V_F)$ **Parallel conductance $g_p = f(V_R)$** **Forward resistance $r_f = f(I_F)$
 $f = 100 \text{ MHz}$** **Diode capacitance $C_T = f(V_R)$** 